

High-Power Probes

High-voltage/current probes and accessories

DATA SHEET

Cascade Microtech's high-power probes provide a complete on-wafer solution for over-temperature, low-contact resistance measurements of power semiconductors. Together with Tesla on-wafer power device characterization system, Cascade Microtech's high-power probes achieve reliable and repeatable on-wafer measurements up to 300 A and 10,000 V.

Safety Notice: The probes discussed within this data sheet are designed to be used on Cascade Microtech Tesla on-wafer power device characterization systems that incorporate a light curtain, safety interlocks and other features required for the safe use of these types of probes. These probes are only meant to be used on Tesla systems or probing systems that have the same or substantially equivalent safety features. If there is any uncertainty with regard to the safety requirements for your application of these types of products or the safety features of your probing system(s), please consult with your company's safety officials.

HIGH-POWER PROBE SELECTION GUIDE

	UHP	HCP		HVP*		
		HCP-1B	HCP-BNC	HVP-3T	HVP-3C	HVP-13
Max. pulsed current	Up to 300 A	100 A	40 A	2 A	5 A	2 A
Voltage	Up to 10,000 V	500 V	500 V	3,000 V (Triax)	3,000 V (Coax)	1,500 V (Triax) 3,000 V (Coax)
Typical probe body residual resistance	≤ 5 mΩ	10 mΩ	10 mΩ	200 mΩ	30 mΩ	30 mΩ
Typical probe life	100,000 touchdowns	100,000 touchdowns	100,000 touchdowns	NA	NA	NA
Probe configuration	single, parallel	single, parallel	single	single	single	single
Typical pad material**	AlSiCu, AlSi, Al	AlSiCu, AlSi, Al, Au***	AlSiCu, AlSi, Al, Au***	AlSiCu, AlSi, Al, Au***	AlSiCu, AlSi, Al, Au***	AlSiCu, AlSi, Al, Au***
Connector type	Insulated HV Banana plug	Dual Banana plug	BNC	Coaxial (Keysight HV Triax)	Coaxial (SHV)	Coaxial BNC (Amphenol 11/16-24 Triax)
Replaceable tip	Yes	Yes	Yes	Yes	Yes	Yes
Configurable tip	Yes	No****	No****	No	No	No

* 5,000 V HVP and 10,000 V HVP probes available upon request.

** For HVP probes, different needle types available depending on the pad materials. Please contact Cascade Microtech for more information.

*** Can be used on Au with BeCu Tips.

**** Configurable tip available as a special request.

UHP PROBE

Cascade Microtech's Ultra-High-Power Probe (UHP), a high-voltage parametric probe, handles both high voltage (up to 10,000 V) and high current (up to 600 A) at a wide temperature range (-55°C to 300°C). The UHP achieves full I-V characterization with one setup and one touchdown. Together with Tesla on-wafer power device characterization system, the UHP fully utilizes the high-voltage/current capability of Agilent B1505A and N1265A Ultra High Current Expanders.

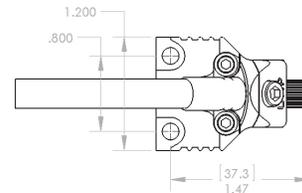
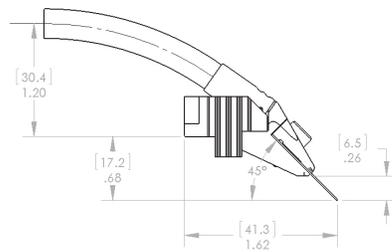
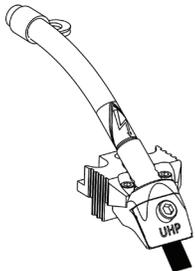


- Coaxial measurements up to 10,000 V and 300 A pulsed (20A DC), without the need for multiple probes and multiple measurement setup changes
- Innovative multi-finger tip design to achieve even distribution of current and minimize pad damage
- Probe current can be doubled up to 600 A when using double probe configuration
- Highly reliable, stable and repeatable measurements with Agilent B1505A and N1265A Ultra High Current Expander

UHP Probe Holder

Maximum voltage	10,000 V DC at 200°C, 8,000 V at 300°C
Maximum current	300 A pulse (600 A in a parallel configuration) / 20 A DC
Operating temperature range	-55°C to 300°C
Connector type	High-voltage Banana (4 mm)
Length of cable	1 m
Positioner compatibility	SUMMIT™ RF positioners
Probe residual resistance	≤ 5 mΩ
Probe insulation resistance	> 10 TΩ at 25°C (chuck temperature) > 3 TΩ at 200°C (chuck temperature) > 1 TΩ at 300°C (chuck temperature)

Physical Dimensions



UHP Probe Tips

Typical contact resistance on AlSiCu	$< 2 \text{ m}\Omega$ (AlSiCu metal layer) for 12 fingers $< 3 \text{ m}\Omega$ (AlSiCu metal layer) for 8 fingers tip $< 6 \text{ m}\Omega$ (AlSiCu metal layer) for 4 fingers tip $< 30 \text{ m}\Omega$ (AlSiCu metal layer) for 1 fingers tip	
Tip material	Tungsten	
Recommended range of overtravel	125-250 μm	
Scrub	~150 μm (at 300 μm overtravel)	
Finger width	Approximately 250 μm	
Finger pitch	650 μm	
Probe tip layouts	12 fingers (300 A)	7400 μm width
	8 fingers (200 A)	4800 μm width
	4 fingers (100 A)	2200 μm width
	1 finger (25 A)	250 μm width

HCP PROBE

Cascade Microtech's High-Current Probe (HCP) reduces probe and/or device destruction at high currents. It supports 10 A DC and up to 100 A of pulsed current. By design, the probe tip minimizes contact resistance at the wafer-to-probe interface to prevent device heating at the tip. The innovative multi-finger probe tip design distributes current evenly over multiple contact points and is joined by a single heat sink that pulls heat from the probe tip.

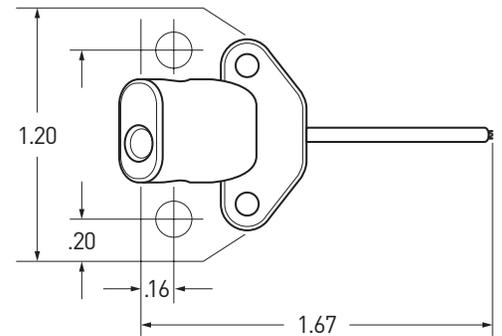
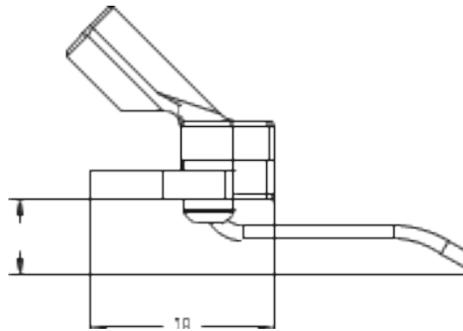
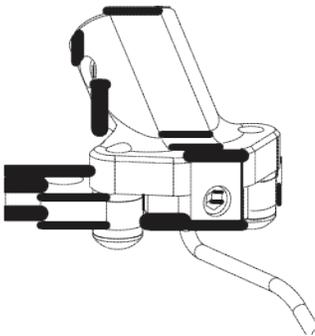
- Minimal contact resistance at the pad-tip junction to reduce heating during measurements, with fewer probe marks
- Measure devices on wafer at high-current conditions over a wide temperature range (-55°C to 300°C)
- Small scrub minimizes damage on Al pad
- Small footprint - tip for small pad probing down to 1 mm x 1 mm pad



HCP Probe Holder

Maximum voltage	500 V DC
Maximum current (DC)	10 A
Maximum current (pulse)	100 A, 1 msec max PW, 1% max duty cycle (BNC: 40 A, 1 msec max PW, 1% max duty cycle)
Total resistance with tip	10 mΩ (typical)
Operating temperature range	-55°C to 300°C
Isolation resistance	> 100 GΩ at 500 V
Connector type	Dual banana jack or BNC
Length of cable	1 m (BNC: 0.76 m)
Positioner compatibility	Summit RF positioner

Physical Dimensions



HCP Probe Tips

Typical contact resistance on Al	20 mΩ
Tip material	Tungsten
Recommended range of overtravel	75-125 μm
Contact force	20 grams per tip (60 grams total) at 100 μm overtravel
Scrub	75 μm

Typical Scrub Mark on Al Pads

The Tesla system HCP probe has been specifically designed for the purpose of minimizing contact resistance, while reducing the amount of probe damage and/or destruction of the device under test. Pictured here is a typical scrub mark on Al pads.

